

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

a transferring chamber including a first mechanism for transferring said substrate; and

a liquid phase film deposition chamber connected to said transferring chamber through a gate; and ~~[[,]]~~

an oxidization furnace connected to said liquid phase film deposition chamber through a piping,

wherein said oxidization furnace ~~liquid phase film deposition chamber~~ is provided with a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said oxidization furnace includes a third mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,~~

~~wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid.~~

2. (Original) A film deposition apparatus according to claim 1,

wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

3. (Original) A film deposition apparatus according to claim 1,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

4. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

a transferring chamber including a first mechanism for transferring the substrate; and

a liquid phase film deposition chamber connected to said transferring chamber through a gate; and [[,]]

an oxidization furnace connected to said liquid phase film deposition chamber through a piping,

wherein said oxidization furnace ~~liquid phase film deposition chamber~~ is provided with ~~via a piping,~~ a second mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table and a shutter for shutting off oxygen to said second mechanism,

wherein said oxidization furnace includes a third mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,~~

~~wherein a period of time in which said oxygen-gettering agent is oxidized is adjusted by opening and closing said lid.~~

5. (Original) A film deposition apparatus according to claim 4,

wherein an inside of said transferring chamber is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

6. (Original) A film deposition apparatus according to claim 4,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

7. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate; and [[,]]

an oxidization furnace connected to said liquid phase film deposition chamber through a piping.

wherein said oxidization furnace ~~liquid phase film deposition chamber~~ is provided with a first mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said oxidization furnace includes a second mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,~~

~~wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid.~~

8. (Previously presented) A film deposition apparatus according to claim 7,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

9. (Previously presented) A film deposition apparatus according to claim 7,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

10 (Currently Amended). A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

a liquid phase film deposition chamber connected to another said transferring chamber through a gate; and [[,]]

an oxidization furnace connected to said liquid phase film deposition chamber through a piping,

wherein said oxidization furnace liquid phase film deposition chamber is provided with ~~-,~~ via ~~a piping,~~ a first mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table and a shutter for shutting off oxygen to said first mechanism,

wherein said oxidization furnace includes a second mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,~~

~~wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid.~~

11. (Previously presented) A film deposition apparatus according to claim 10,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said liquid phase film deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

12. (Previously presented) A film deposition apparatus according to claim 10,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

13. (Currently Amended) A film deposition apparatus comprising:

- a stock chamber for loading or unloading a substrata;
- a transferring chamber for transferring said substrate; and
- an EL material deposition chamber connected to said transferring chamber through a gate;

and [[,]]

an oxidization furnace connected to said EL material deposition chamber through a piping,

wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,

wherein said oxidization furnace includes a mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent;~~

~~wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid.~~

14. (Original) A film deposition apparatus according to claim 13,

wherein an inside of said transferring chamber is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

15. (Original) A film deposition apparatus according to claim 13,

wherein said transferring chamber is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

16. (Currently Amended) A film deposition apparatus comprising:

a stock chamber for loading or unloading a substrate;

two transferring chambers each connected to said stock chamber through a gate;

a vapor phase film deposition chamber connected to one of said two transferring chambers through a gate; and

an EL material deposition chamber connected to another said transferring chamber through a gate; and [[,]]

an oxidization furnace connected to said EL material deposition chamber through a piping,

wherein said EL material deposition chamber is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table,

wherein said oxidization furnace includes a mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said second mechanism includes an oxidization cell having a lid and an oxygen gettering agent,~~

~~wherein a period of time in which said oxygen gettering agent is oxidized is adjusted by opening and closing said lid.~~

17. (Previously presented) A film deposition apparatus according to claim 16,

wherein an inside of one of said transferring chambers is kept under a reduced pressure and said EL material deposition chamber is filled with an inert gas and is kept under atmospheric pressure or in a pressurized state.

18. (Previously presented) A film deposition apparatus according to claim 16,

wherein one of said transferring chambers is connected to a calcining chamber through a gate, and said calcining chamber is provided with a mechanism for turning said substrate upside down.

19-30 (Cancelled).

31 (Previously presented) A film deposition apparatus according to claim 1,

wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

32 (Previously presented) A film deposition apparatus according to claim 1,

wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

33 (Previously presented) A film deposition apparatus according to claim 1,

wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

34 (Previously presented) A film deposition apparatus according to claim 4,

wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

35 (Previously presented) A film deposition apparatus according to claim 4,
wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

36 (Previously presented) A film deposition apparatus according to claim 4,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

37 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

38 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

39 (Previously presented) A film deposition apparatus according to claim 7,
wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

40 (Previously presented) A film deposition apparatus according to claim 10,
wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

41 (Previously presented) A film deposition apparatus according to claim 10, wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

42 (Previously presented) A film deposition apparatus according to claim 10, wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.

43 (Previously presented) A film deposition apparatus according to claim 13, wherein said EL material deposition chamber is provided with a spin coater for forming an EL layer.

44 (Previously presented) A film deposition apparatus according to claim 13, wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

45 (Previously presented) A film deposition apparatus according to claim 16, wherein said EL material deposition chamber is provided with a spin coater for forming an EL layer.

46 (Previously presented) A film deposition apparatus according to claim 16, wherein said EL material deposition chamber is provided with a nozzle for forming an EL layer.

47 - 52 (Canceled)

53 (Currently Amended) A film deposition apparatus according to claim 1, wherein said third ~~second~~ mechanism includes a heater.

54 (Currently Amended) A film deposition apparatus according to claim 4, wherein said third ~~second~~ mechanism includes a heater.

55 (Previously Presented) A film deposition apparatus according to claim 7, wherein said second mechanism includes a heater.

56 (Previously Presented) A film deposition apparatus according to claim 10, wherein said second mechanism includes a heater.

57 (Currently Amended) A film deposition apparatus according to claim 13, wherein said ~~second~~ mechanism includes a heater.

58 (Currently Amended) A film deposition apparatus according to claim 16, wherein said ~~second~~ mechanism includes a heater.

59. (Currently Amended) A film deposition apparatus comprising:
a liquid phase film deposition chamber; [[,]]

an oxidization furnace connected to said liquid phase film deposition chamber through a piping,

wherein said oxidization furnace ~~liquid phase film deposition chamber~~ is provided with a cell which contains an element belonging to Group 1 or 2 of the periodic table a mechanism for oxidizing an element belonging to Group 1 or 2 of the periodic table,

wherein said oxidization furnace includes a mechanism for heating said element belonging to Group 1 or 2 of the periodic table.

~~wherein said mechanism includes an oxidization cell having a lid and an oxygen-gettering agent,~~

~~wherein a period of time in which said oxygen-gettering agent is oxidized is adjusted by opening and closing said lid.~~

60 (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is a chamber for depositing an EL material.

61 (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is provided with a spin coater for forming an EL layer.

62 (Previously Presented) A film deposition apparatus according to claim 59, wherein said liquid phase film deposition chamber is provided with a nozzle for forming an EL layer.